

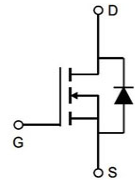
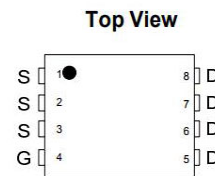
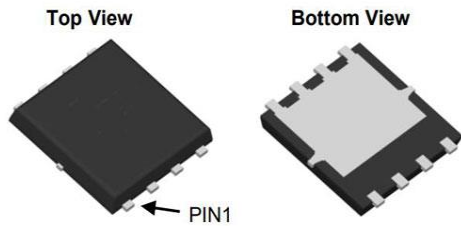
**General Description**

30V /60A Single N Power MOSFET

 Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5\text{ V}$ 

Pb-free lead plating; RoHS compliant

$V_{DS}$	30	V
$R_{DS(on),TYP@V_{GS}=10V}$	6.0	mΩ
$R_{DS(on),TYP@V_{GS}=4.5}$	9.5	mΩ
$I_D$	60	A



Part ID	Package Type	Marking	Tape and reel information
ACN6362	DFN5x6	6362	3000


 100% UIS Tested  
 100% kg tested

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	20	±V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	A
		$T_A=70^\circ\text{C}$	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	96.0	
Avalanche Current <sup>G</sup>	$I_{AR}$	19.2	
Repetitive avalanche energy $L=0.1\text{mH}$ <sup>G</sup>	$E_{AR}$	44.2	mJ
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	21	32	°C/W
Maximum Junction-to-Ambient <sup>A</sup>		Steady State	43	
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	12	20	°C/W

**STATIC PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = -250uA, V <sub>GS</sub> = 0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	uA
					5	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250μA	1.1	1.7	2.2	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		6.0	8.6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		9.5	12.3	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		75		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =190V		0.72	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				60	A

**DYNAMIC PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		820	1000	pF
C <sub>oss</sub>	Output Capacitance			340	418	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			40	47	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz			1.2	Ω

**SWITCHING PARAMETERS**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		6.1		nC
Q <sub>g</sub> 4.5V)	Total Gate Charge			3.05		
Q <sub>gs</sub>	Gate Source Charge			1.68		
Q <sub>gd</sub>	Gate Drain Charge			2.4		
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		5.5		ns
t <sub>r</sub>	Turn-On Rise Time			4.4		
t <sub>D(off)</sub>	Turn-Off DelayTime			15.4		
t <sub>f</sub>	Turn-Off Fall Time			4.95		
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-8A, dI/dt=500A/μs		11		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =18A, dI/dt=500A/μs		19		nC

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

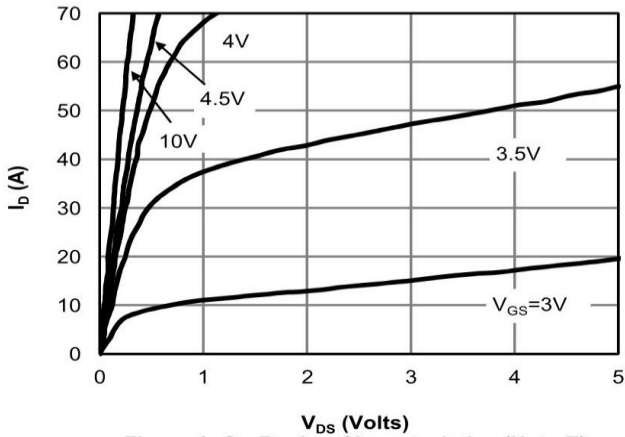


Figure 1: On-Region Characteristics (Note E)

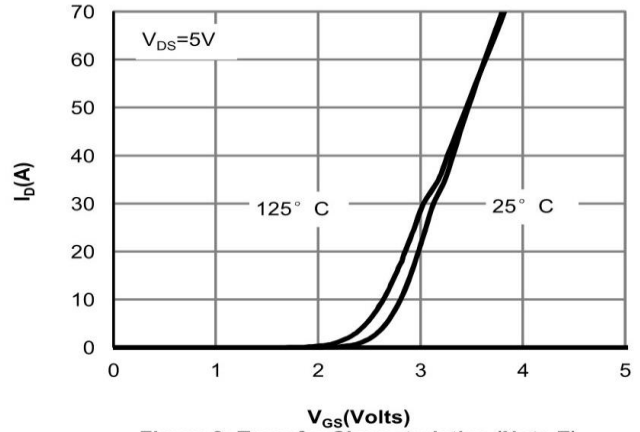


Figure 2: Transfer Characteristics (Note E)

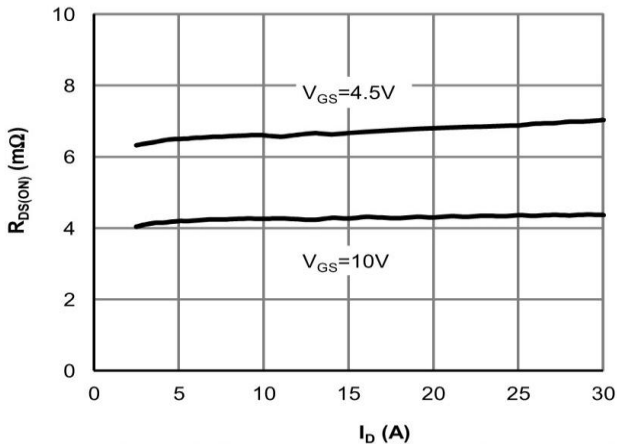


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

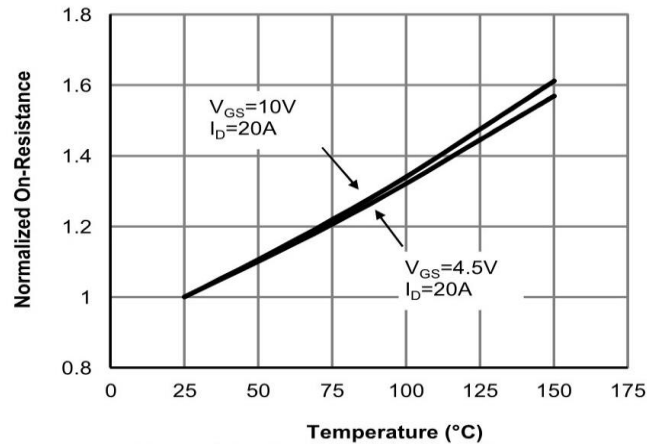


Figure 4: On-Resistance vs. Junction Temperature (Note E)

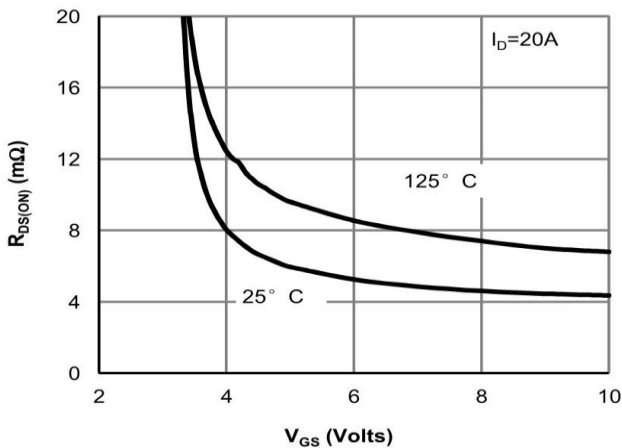


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

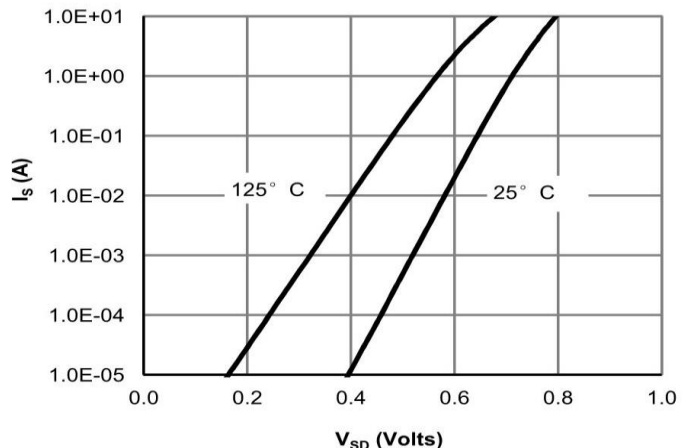


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

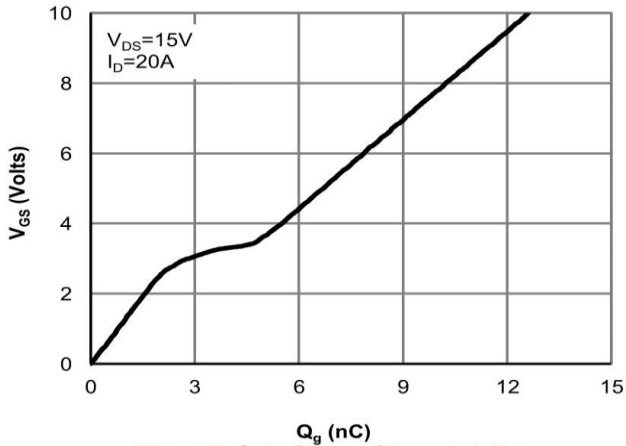


Figure 7: Gate-Charge Characteristics

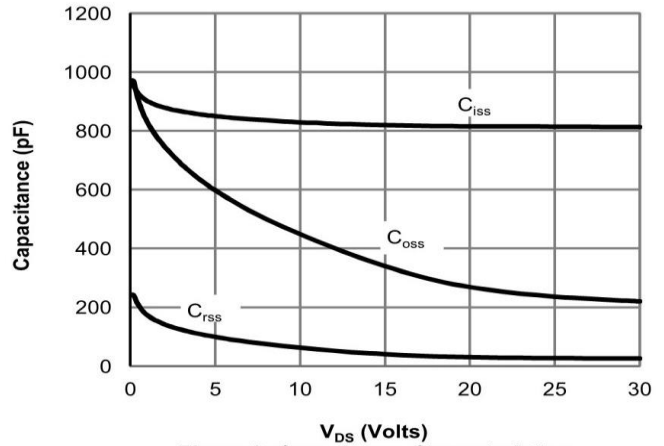


Figure 8: Capacitance Characteristics

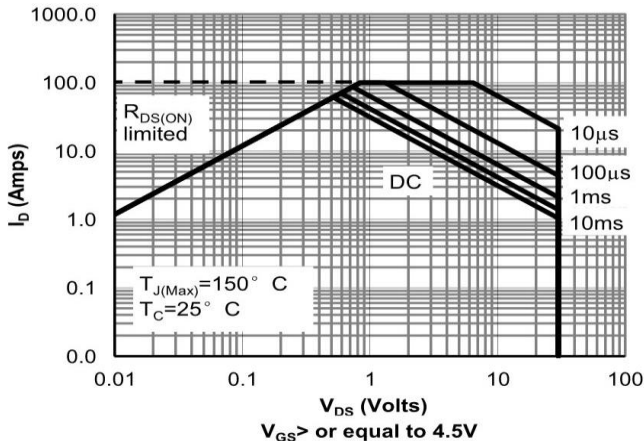


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

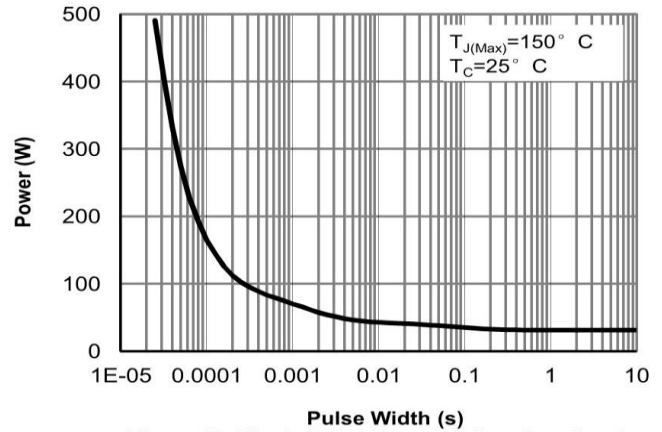


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

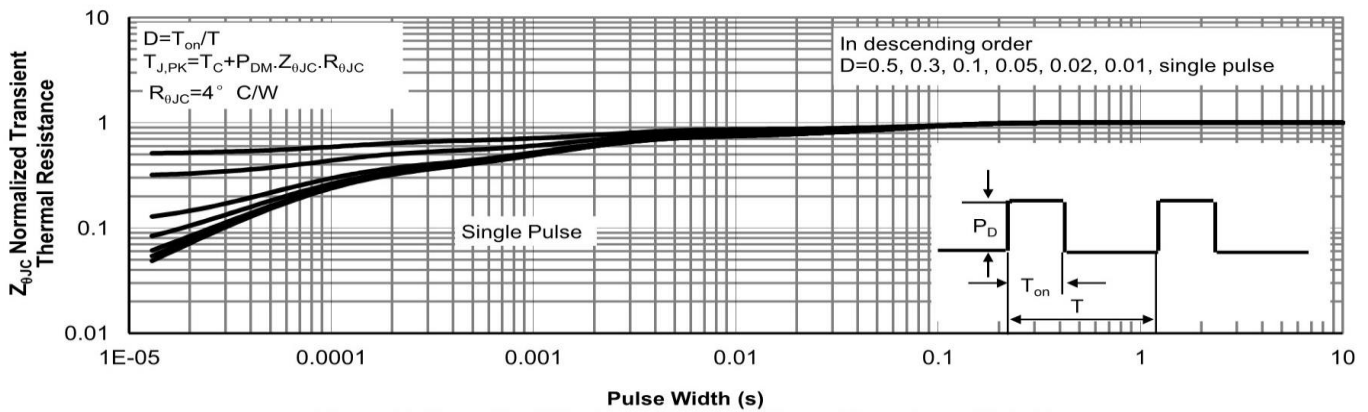


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)